Tantation	DMC366A3		
Tentative	Total pages	page	

DMC366A3

Silicon NPN epitaxial planar type (Tr1)

Silicon NPN epitaxial planar type (Tr2)

For digital circuits

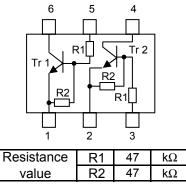
Marking Symbol : J0

Package Code : SSSMini6-F2-B

Absolute Maximum Ratings Ta = 25 °C Parameter Symbol Rating Unit Collector-base voltage (Emitter open) VCBO 50 V Tr1 Collector-emitter voltage (Base open) VCEO 50 V Tr2 Collector current IC 80 mΑ PT 125 Total power dissipation mW Τj 150 °C Overall Junction temperature °C Storage temperature Tstg -55 to +150

Note: 1. *1 Measuring on substrate at 17 mm × 10 mm × 1 mm

Internal Connection



	Pin	na	am	ie
1.	Emitter(Tr1)		4.	Collector(Tr2)
2.	Emitter(Tr2)		5.	Base(Tr1)
3.	Base(Tr2)		6.	Collector(Tr1)

Electrical Characteristics Ta = 25 °C±3 °C Tr1.Tr2

Symbol	Conditions	Min	Tvn	Max	Unit	
VCBO	$IC = 10 \ \mu A, IE = 0$	50	190	wax	V	
VCEO	IC = 2 mA, IB = 0	50			V	
ICBO	VCB = 50 V, IE = 0			0.1	μA	
ICEO	VCE = 50 V, IB = 0			0.5	μA	
IEBO	VEB = 6 V, IC = 0			0.1	mA	
hFE	VCE = 10 V, IC = 5 mA	80			-	
VCE(sat)	IC = 10 mA, IB = 0.5 mA			0.25	V	
Vi(on)	VCE = 0.2 V, IC = 5 mA	3.6			V	
Vi(off)	VCE = 5 V, IC = 100 µA		0.8	v		
R1		-30%	47	+30%	kΩ	
R1/R2		0.8	1.0	1.2	-	
	VCEO ICBO ICEO IEBO hFE VCE(sat) Vi(on) Vi(off) R1	VCBO IC = 10 μ A, IE = 0 VCEO IC = 2 mA, IB = 0 ICBO VCB = 50 V, IE = 0 ICEO VCE = 50 V, IB = 0 IEBO VEB = 6 V, IC = 0 hFE VCE = 10 V, IC = 5 mA VCE(sat) IC = 10 mA, IB = 0.5 mA Vi(on) VCE = 0.2 V, IC = 5 mA Vi(off) VCE = 5 V, IC = 100 μ A	VCBO IC = 10 μ A, IE = 0 50 VCEO IC = 2 mA, IB = 0 50 ICBO VCB = 50 V, IE = 0 50 ICEO VCE = 50 V, IB = 0 50 IEBO VEB = 6 V, IC = 0 50 hFE VCE = 10 V, IC = 5 mA 80 VCE(sat) IC = 10 mA, IB = 0.5 mA 3.6 Vi(off) VCE = 5 V, IC = 100 μ A 730%	VCBO IC = 10 μ A, IE = 0 50 VCEO IC = 2 mA, IB = 0 50 ICBO VCB = 50 V, IE = 0 50 ICEO VCE = 50 V, IB = 0 10 IEBO VEB = 6 V, IC = 0 10 hFE VCE = 10 V, IC = 5 mA 80 VCE(sat) IC = 10 mA, IB = 0.5 mA 3.6 Vi(on) VCE = 5 V, IC = 100 μ A 7.30% R1 -30% 47	VCBO IC = 10 μ A, IE = 0 50 51 VCEO IC = 2 mA, IB = 0 50 0.1 ICBO VCE = 50 V, IE = 0 0.1 ICEO VCE = 50 V, IB = 0 0.5 IEBO VEB = 6 V, IC = 0 0.1 hFE VCE = 10 V, IC = 5 mA 80 VCE(sat) IC = 10 mA, IB = 0.5 mA 0.25 Vi(on) VCE = 5 V, IC = 5 mA 3.6 Vi(off) VCE = 5 V, IC = 100 μ A 0.8 R1 -30% 47	

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. *1 Pulse measurement

Packing

Embossed type (Thermo-compression sealing) R specification : 10 000 pcs / reel

2010.3.15 2010.11
Prepared Revis

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